## Soufiane Karrakchou

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/7296135/publications.pdf

Version: 2024-02-01

10 papers	82 citations	1307366 7 h-index	1588896 8 g-index
10 all docs	10 docs citations	10 times ranked	69 citing authors

#	Article	lF	CITATIONS
1	Natural Boron and <sup>10</sup> B-Enriched Hexagonal Boron Nitride for High-Sensitivity Self-Biased Metal–Semiconductor–Metal Neutron Detectors. ACS Omega, 2022, 7, 804-809.	1.6	6
2	Monolithic Free-Standing Large-Area Vertical III-N Light-Emitting Diode Arrays by One-Step h-BN-Based Thermomechanical Self-Lift-Off and Transfer. ACS Applied Electronic Materials, 2021, 3, 2614-2621.	2.0	8
3	MOVPE of GaN-based mixed dimensional heterostructures on wafer-scale layered 2D hexagonal boron nitride—A key enabler of III-nitride flexible optoelectronics. APL Materials, 2021, 9, .	2.2	9
4	Towards P-Type Conduction in Hexagonal Boron Nitride: Doping Study and Electrical Measurements Analysis of hBN/AlGaN Heterojunctions. Nanomaterials, 2021, 11, 211.	1.9	14
5	Control of the Mechanical Adhesion of Ill–V Materials Grown on Layered h-BN. ACS Applied Materials & Interfaces, 2020, 12, 55460-55466.	4.0	14
6	Effectiveness of selective area growth using van der Waals h-BN layer for crack-free transfer of large-size III-N devices onto arbitrary substrates. Scientific Reports, 2020, 10, 21709.	1.6	12
7	Heterogeneous Integration: Novel Scalable Transfer Approach for Discrete Illâ€Nitride Devices Using Waferâ€Scale Patterned hâ€BN/Sapphire Substrate for Pickâ€andâ€Place Applications (Adv. Mater. Technol.) Tj B	T <b>Q</b> .pl 10	0.7 <b>&amp;</b> 4314 rg <mark>8</mark> T
8	Nanopyramid-based absorber to boost the efficiency of InGaN solar cells. Solar Energy, 2019, 190, 93-103.	2.9	7
9	Novel Scalable Transfer Approach for Discrete IIIâ€Nitride Devices Using Waferâ€Scale Patterned hâ€BN/Sapphire Substrate for Pickâ€andâ€Place Applications. Advanced Materials Technologies, 2019, 4, 1900164.	3.0	10
10	Investigation of Sc2O3 Based All-Solid-State EIS Structure for AlGaN/GaN HEMT pH Sensor., 2019,,.		2